

 <p>FORM PTO 1449 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE</p> <p>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</p> <p>(USE SEVERAL SHEETS IF NECESSARY)</p>	ATTY. DOCKET NO. SEPP9.001APC	APPLICATION NO. 09/787,082
	APPLICANT Leskela et al.	
	FILING DATE June 28, 2001	GROUP 1765

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)	
RK	1.	Vehkamäki et al., <u>Growth of SrTiO₃ and BaTiO₃ Thin Films by Atomic Layer Deposition</u> , Electrochemical and Solid-State Letters, 2 (10) pp. 504-506 (1999)
RK	2.	Nakano et al., <u>Digital chemical vapor deposition of SiO₂</u> , Appl. Phys. Lett 57 (11), September 10, 1990, pp. 1096-1098
RK	3.	S.M. Bedair, <u>Atomic layer epitaxy deposition processes</u> , J. Vac. Sci Technol. B 12(1), Jan/Feb 1994, pp. 179-185

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EXAMINER	/Robert Kunemund/	DATE CONSIDERED	07/03/2006
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